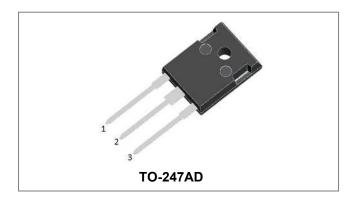


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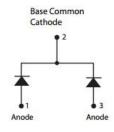
## SDUR60P60WT ULTRAFAST RECTIFIER



## **Applications**

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

#### **Circuit Diagram**



#### **Features**

- Ultra-Fast switching
- · High current capability
- Low reverse leakage current
- High surge current capability
- This is a Pb free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{R} \end{array}$	-	600	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=70°C, rectangular wave form	30(Per Leg) 60(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse	200	А

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V <sub>F1</sub>	@ 15A, Pulse, T <sub>J</sub> = 25°C	1.20	-	V
		@ 30A, Pulse, T <sub>J</sub> = 25°C	1.50	1.70	•
Reverse Current	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> =25°C	0.03	150	uA
(Per Leg)*	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> =125°C	8	1	mA
Reverse Recovery Time (Per Leg)	t <sub>rr</sub>	I <sub>F</sub> =500mA,I <sub>R</sub> =1A,and I <sub>m</sub> =250mA	40	50	ns

<sup>\*</sup> Pulse width < 300 μs, duty cycle < 2%

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com
     sales@ smc-diodes.com



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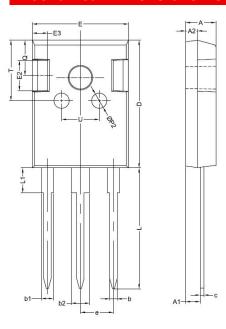


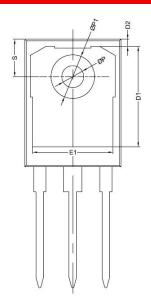


# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	0.34	°C/W
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

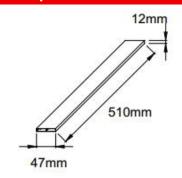
## **Mechanical Dimensions TO-247AD**



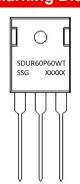


SYMBOL	Millimeters					
STIVIBUL	MIN.	TYP.	MAX.			
Α	4.80	5.00	5.20			
A1	2.20	2.41	2.61			
A2	1.90	2.00	2.10			
b	1.10	1.20	1.40			
b1	1.80	2.00	2.20			
b2	2.80	3.00	3.20			
С	0.50	0.60	0.75			
D	20.30	21.00	21.20			
D1		16.55				
D2		1.20				
D2 E	15.45	15.80	16.00			
E1		13.30				
E2		5.00				
E3		2.50				
е		5.44				
L	19.42	19.92	20.70			
L1		4.13				
Р	3.50	3.60	3.70			
P1	7.1		7.40			
P2		2.50				
Q		5.80				
Q S T	6.05	6.15	6.25			
T		10.00				
U		6.20				

# **Tube Specification**



# **Marking Diagram**



Where XXXXX is YYWWL

SDUR = Device Type = Forward Current (60A) 60

60

= Reverse Voltage (600V) = Configuration WT = SSG SSG = Year

YY  $\mathsf{W}\mathsf{W}$ = Week = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

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- http://www.smc-diodes.com sales@ smc-diodes.com •

#### SDUR60P60WT



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# **Ordering Information:**

Device	Package	Shipping	
SDUR60P60WT	TO-247AD(Pb-Free)	25pcs / tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

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